

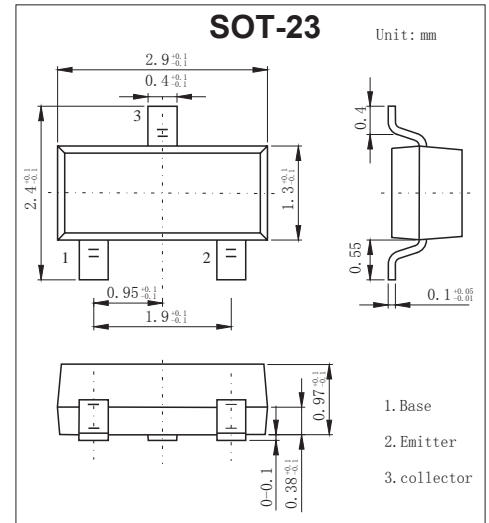
## SOT-23 Plastic-Encapsulate Transistors

### Features

- High breakdown voltage
- PNP Transistors

### MECHANICAL DATA

- Case style: SOT-23 -3molded plastic
- Mounting position: any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-55	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-150	mA
Collector dissipation	P <sub>C</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-50 to 150	°C

### PACKAGE INFORMATION

Device	Package	Shipping
2SA1179	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -100uA , I <sub>E</sub> = 0A	-55			V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1mA , I <sub>B</sub> = 0 A	-50			V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100uA , I <sub>C</sub> = 0A	-5			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -35V , I <sub>E</sub> = 0A			-0.1	μ A
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V , I <sub>C</sub> = 0			-0.1	μ A
DC current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -6V , I <sub>C</sub> = -1mA	200		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -50mA , I <sub>B</sub> = -5mA			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -50mA , I <sub>B</sub> = -5mA			-1.0	V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -6V , I <sub>E</sub> =0 , f = 1MHz		4.0		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -6V , I <sub>C</sub> = -10mA		180		MHz

### ■ Marking

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